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	HIRA.0204	10/549,683
	APPLICANT	
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U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
						YES	NO

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		Japanese Office Action dated June 23, 2009
		Norio Onojima et al., "Lattice Relaxation Process of AlN Growth on Atomically Flat 6H-SiC Substrate in Molecular Beam Epitaxy", Journal of Crystal Growth (2002), pp. 1012-1016
		Steve Wright et al., "Reduction of Oxides on Silicon by Heating in a Gallium Molecular Beam at 800°C", Appl. Phys. Lett, Vol. 36, No. 3, 1 February 1980, pp. 210-211
EXAMINER		DATE CONSIDERED

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